

MITSUBISHI TRANSISTOR MODULES

QM100DY-HBK

HIGH POWER SWITCHING USE
INSULATED TYPE

QM100DY-HBK



- **IC** Collector current **100A**
- **VCEX** Collector-emitter voltage **600V**
- **hFE** DC current gain **750**
- **Insulated Type**
- **UL Recognized**

Yellow Card No. E80276 (N)

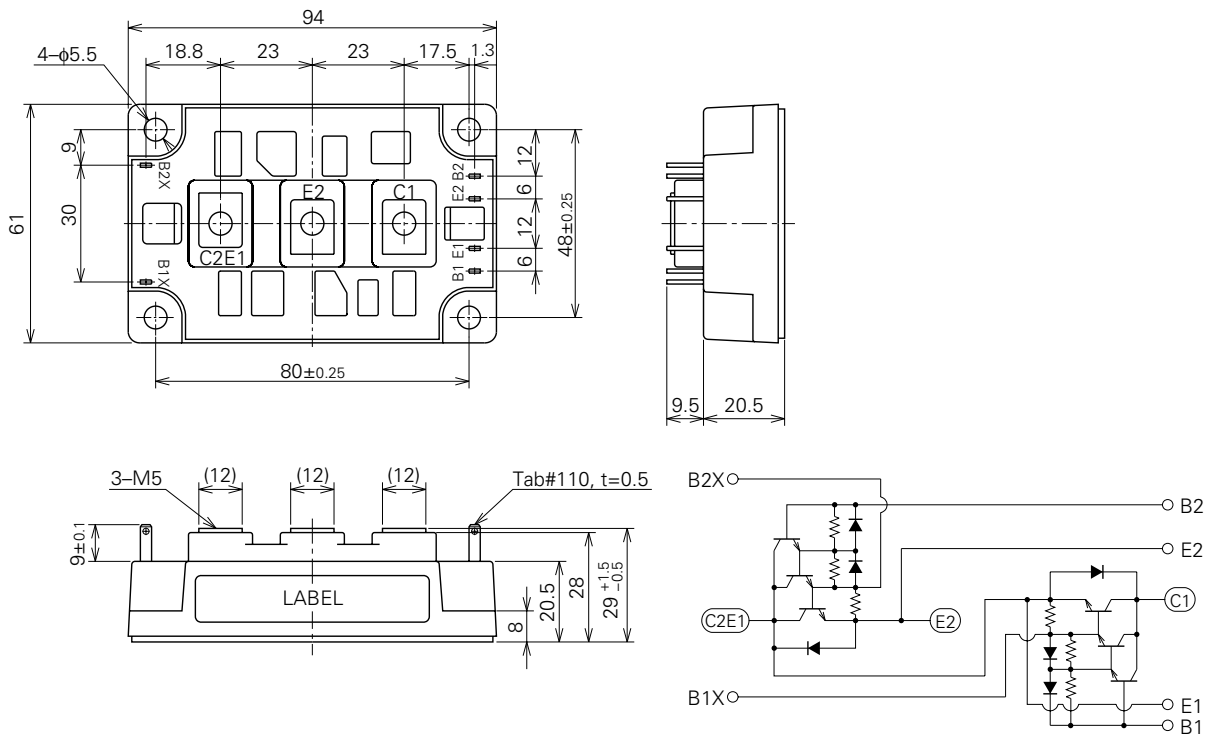
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APPLICATION

Inverters, Servo drives, DC motor controllers, NC equipment, Welders

OUTLINE DRAWING & CIRCUIT DIAGRAM

Dimensions in mm



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ABSOLUTE MAXIMUM RATINGS (Tj=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Ratings	Unit
VCEX (SUS)	Collector-emitter voltage	IC=1A, VEB=2V	600	V
VCEX	Collector-emitter voltage	VEB=2V	600	V
VCBO	Collector-base voltage	Emitter open	600	V
VEBO	Emitter-base voltage	Collector open	7	V
IC	Collector current	DC	100	A
-IC	Collector reverse current	DC (forward diode current)	100	A
PC	Collector dissipation	Tc=25°C	620	W
IB	Base current	DC	6	A
-ICSM	Surge collector reverse current (forward diode current)	Peak value of one cycle of 60Hz (half wave)	1000	A
Tj	Junction temperature		-40~+150	°C
Tstg	Storage temperature		-40~+125	°C
Viso	Isolation voltage	Charged part to case, AC for 1 minute	2500	V
—	Mounting torque	Main terminal screw M5	1.47~1.96	N·m
			15~20	kg·cm
		Mounting screw M5	1.47~1.96	N·m
			15~20	kg·cm
—	Weight	Typical value	420	g

ELECTRICAL CHARACTERISTICS (Tj=25°C, unless otherwise noted)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
ICEX	Collector cutoff current	VCE=600V, VEB=2V	—	—	2.0	mA
ICBO	Collector cutoff current	VCB=600V, Emitter open	—	—	2.0	mA
IEBO	Emitter cutoff current	VEB=7V	—	—	100	mA
VCE (sat)	Collector-emitter saturation voltage	IC=100A, IB=0.13A	—	—	2.5	V
VBE (sat)	Base-emitter saturation voltage		—	—	3.0	V
-VCEO	Collector-emitter reverse voltage	-IC=100A (diode forward voltage)	—	—	1.8	V
hFE	DC current gain	IC=100A, VCE=2.5V	750	—	—	—
ton	Switching time	VCC=300V, IC=100A, IB1=0.2A, -IB2=2.0A	—	—	2.5	μs
ts			—	—	10	μs
tf			—	—	2.0	μs
Rth (j-c) Q	Thermal resistance (junction to case)	Transistor part (per 1/2 module)	—	—	0.2	°C/W
Rth (j-c) R		Diode part (per 1/2 module)	—	—	0.65	°C/W
Rth (c-f)	Contact thermal resistance (case to fin)	Conductive grease applied (per 1/2 module)	—	—	0.1	°C/W